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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100bdgna-u0

O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

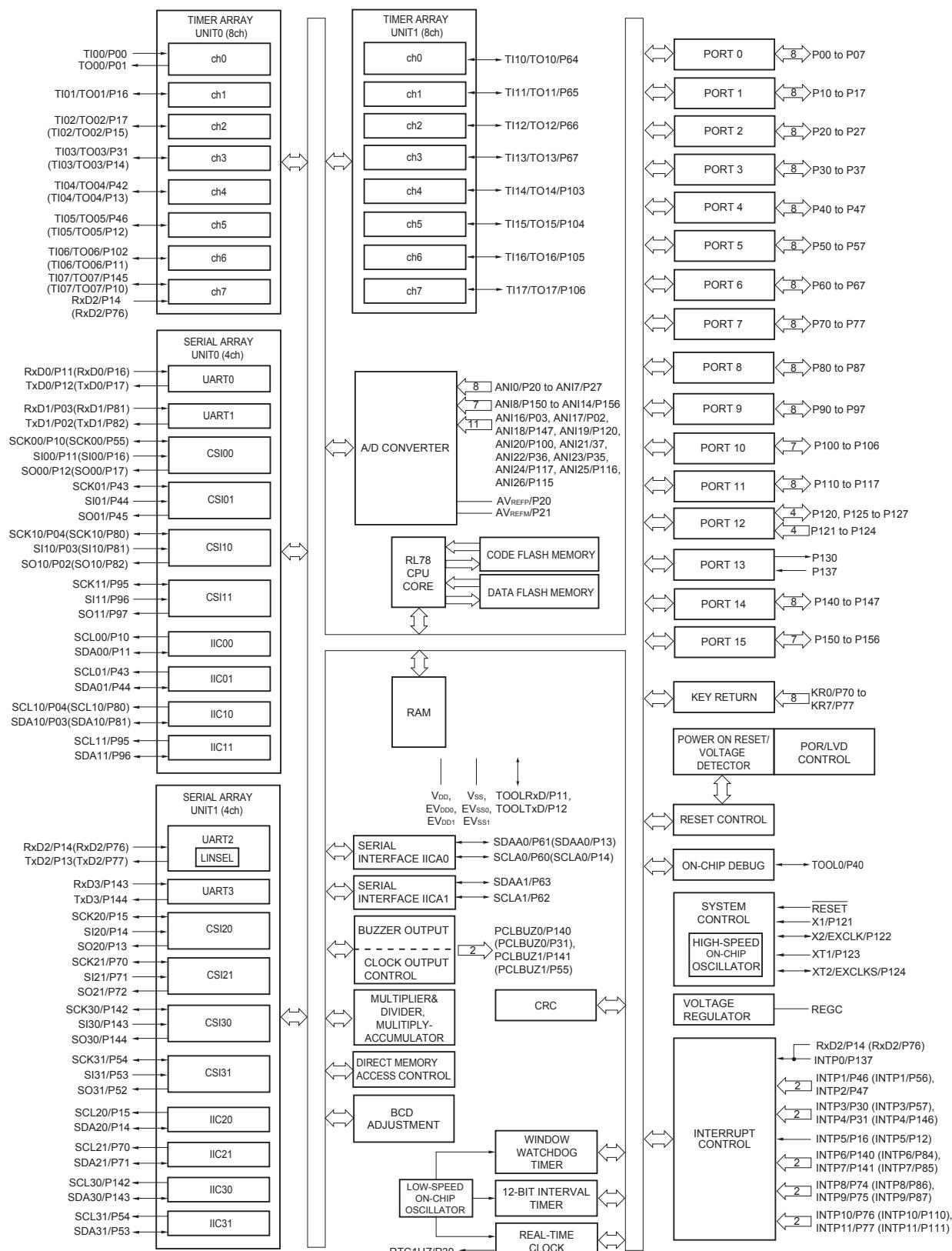
(7/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
52 pins	52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)	Mounted	A	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAF#V0, R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0, R5F100JJFAFA#V0, R5F100JKAFA#V0, R5F100JLAFA#V0 R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAF#X0, R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0, R5F100JJFAFA#X0, R5F100JKAFA#X0, R5F100JLAFA#X0 R5F100JCDSA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0, R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0, R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0 R5F100JCDSA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0, R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0, R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0 R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0, R5F100JFGFA#V0, R5F100JGGFA#V0, R5F100JHGFA#V0, R5F100JJGFA#V0 R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0, R5F100JFGFA#X0, R5F100JGGFA#X0, R5F100JHGFA#X0, R5F100JJGFA#X0
			D	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAF#V0, R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0, R5F101JJFAFA#V0, R5F101JKAFA#V0, R5F101JLAFA#V0 R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAF#X0, R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0, R5F101JJFAFA#X0, R5F101JKAFA#X0, R5F101JLAFA#X0 R5F101JCDSA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0, R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0, R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0 R5F101JCDSA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0, R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0, R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$) (2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I _{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	I _{OH2}	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
	I _{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	I _{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T _A	In normal operation mode	-40 to +85	°C	
		In flash memory programming mode			
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.
3. When high-speed system clock and subsystem clock are stopped.
4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $\text{AMPHS1} = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz

$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH} : High-speed on-chip oscillator clock frequency

3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator and subsystem clock are stopped.
4. When high-speed system clock and subsystem clock are stopped.
5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz
 $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH} : High-speed on-chip oscillator clock frequency

3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

Notes 1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.
3. When high-speed system clock and subsystem clock are stopped.
4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $AMPHS1 = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz

$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

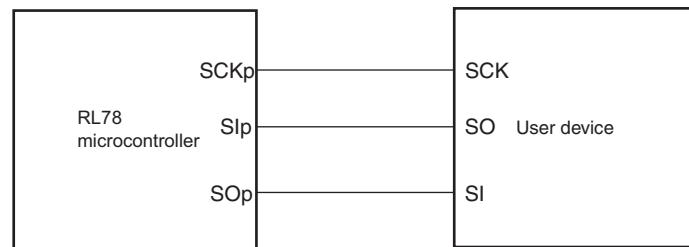
(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

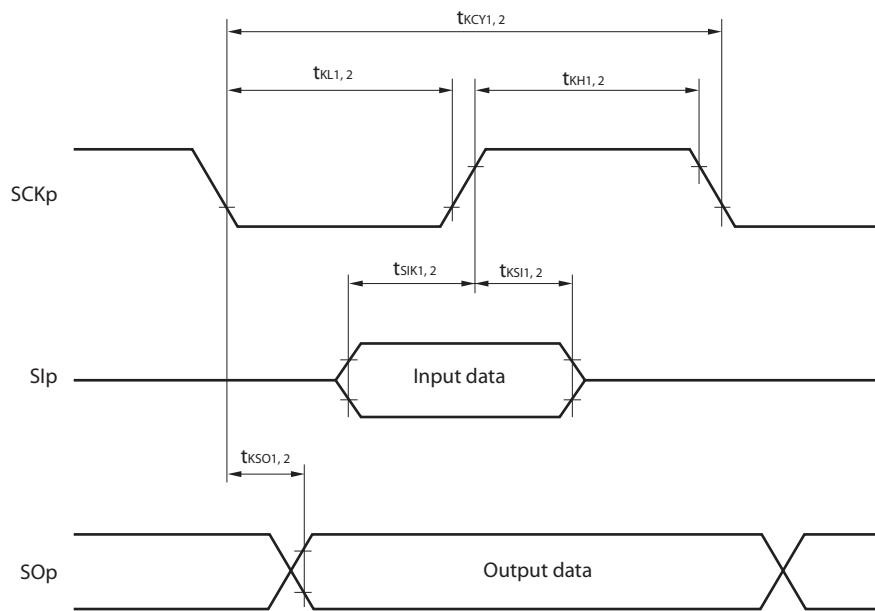
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t _{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V $\leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			2.4 V $\leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			1.8 V $\leq EV_{DD0} \leq 5.5$ V	500		500		1000		ns
			1.7 V $\leq EV_{DD0} \leq 5.5$ V	1000		1000		1000		ns
			1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		1000		1000		ns
SCKp high-/low-level width	t _{Kh1} , t _{kl1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 38		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
Slp setup time (to SCKp↑) <small>Note 1</small>	t _{SIK1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	75		110		110		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	110		110		110		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	220		220		220		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		220		220		ns	
Slp hold time (from SCKp↑) <small>Note 2</small>	t _{ksi1}	1.7 V $\leq EV_{DD0} \leq 5.5$ V	19		19		19		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		19		19		ns	
Delay time from SCKp↓ to SOp output <small>Note 3</small>	t _{ks01}	1.7 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		25		25		25	ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		—		25		25	ns	

- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SCKp and SOp output lines.

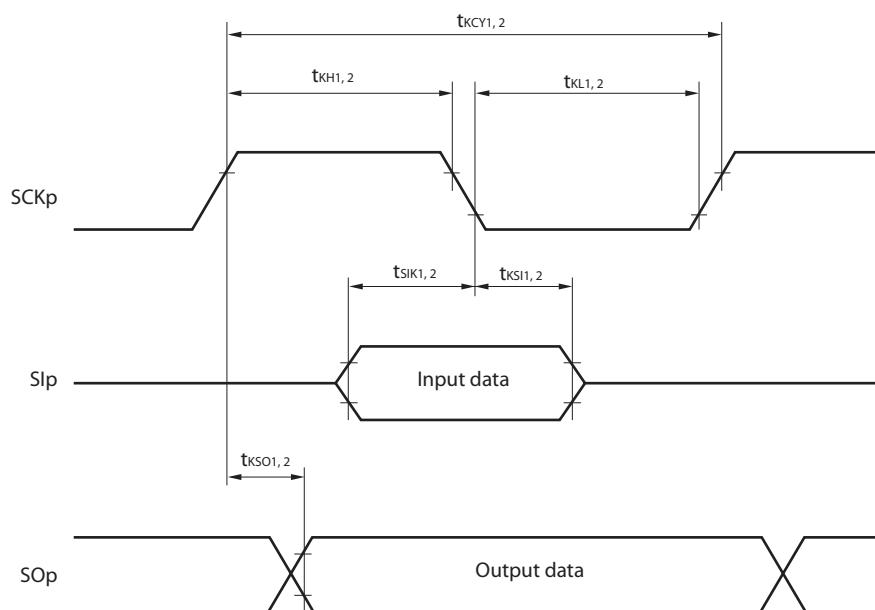
Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

CSI mode connection diagram (during communication at same potential)

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

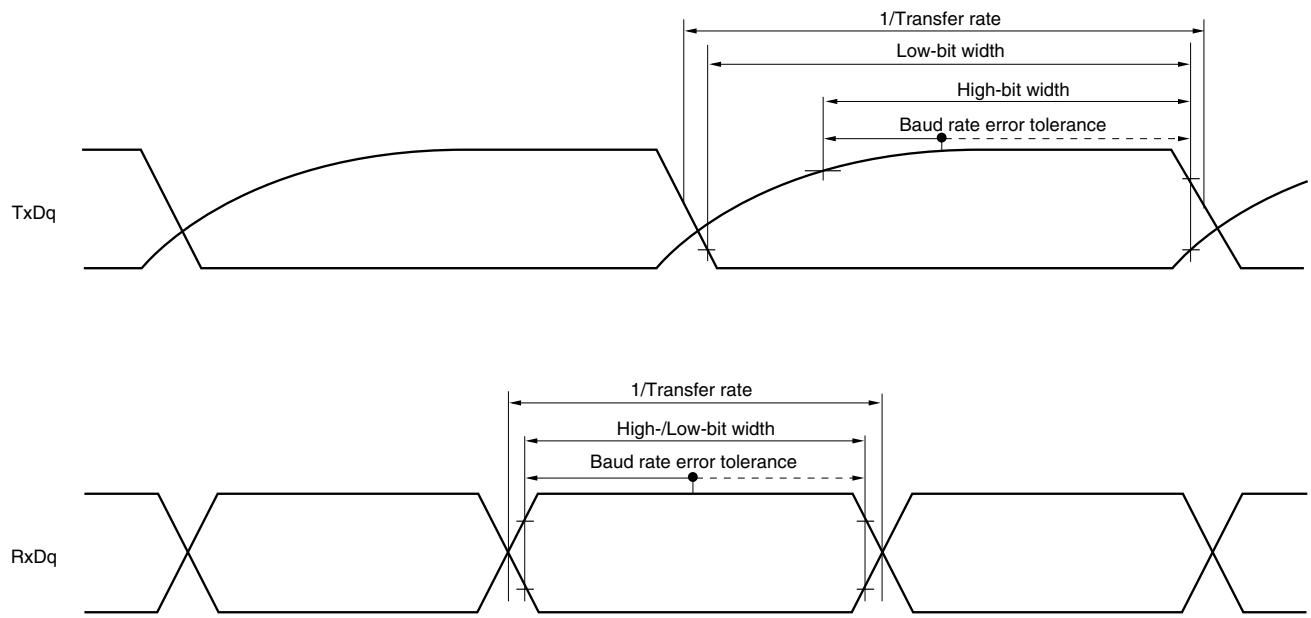


- Remarks**
1. p: CSI number ($p = 00, 01, 10, 11, 20, 21, 30, 31$)
 2. m: Unit number, n: Channel number ($mn = 00$ to $03, 10$ to 13)

(5) During communication at same potential (simplified I²C mode) (1/2) $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

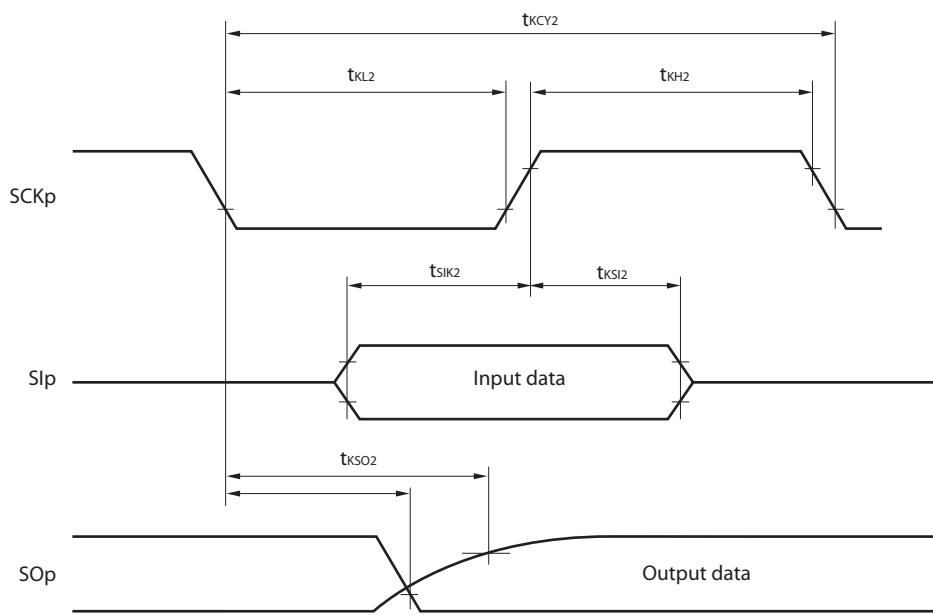
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		250 Note 1		250 Note 1		kHz
Hold time when SCL _r = "L"	t _{LOW}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns
Hold time when SCL _r = "H"	t _{HIGH}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

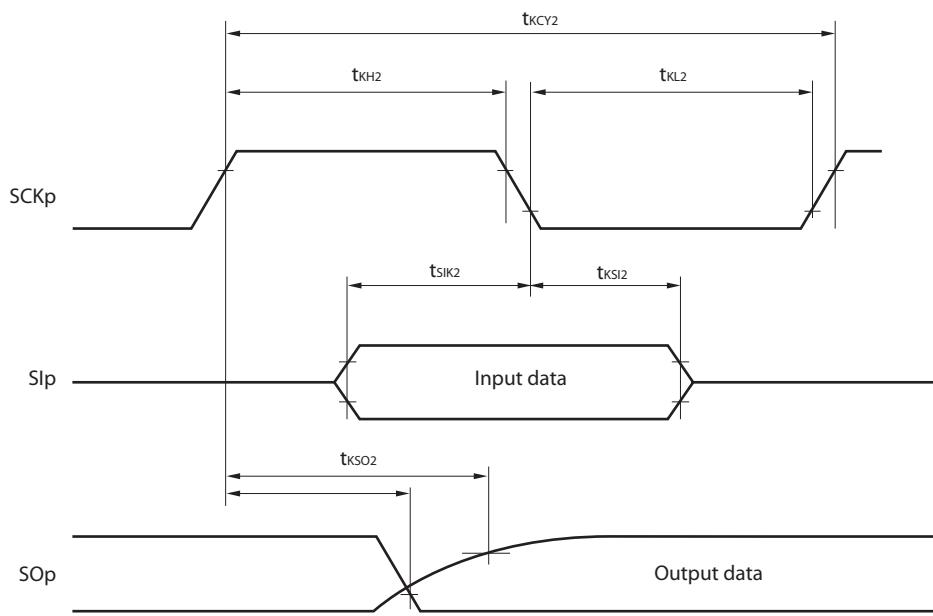
UART mode bit width (during communication at different potential) (reference)

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,
 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 0$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 1$.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 1$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 0$.)



- Remarks**
1. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number,
n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

2.5.2 Serial interface IICA

(1) I²C standard mode $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCLA0 clock frequency	f _{SCL}	Standard mode: $f_{CLK} \geq 1 \text{ MHz}$	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
			1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
			1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
			1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	0	100	0	100	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.7	—	4.7	—	μs	
Hold time ^{Note 1}	t _{HD:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.0	—	4.0	—	μs	
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.7	—	4.7	—	μs	
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.0	—	4.0	—	μs	
Data setup time (reception)	t _{SU:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	250	—	250	—	250	—	ns	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	250	—	250	—	250	—	ns	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	250	—	250	—	250	—	ns	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	250	—	250	—	ns	
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	0	3.45	0	3.45	μs	
Setup time of stop condition	t _{SU:STO}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.0	—	4.0	—	4.0	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.0	—	4.0	—	μs	
Bus-free time	t _{BUF}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	4.7	—	4.7	—	4.7	—	μs	
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—	—	4.7	—	4.7	—	μs	

(Notes, Caution and Remark are listed on the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP}	Reference voltage (+) = V_{DD}	Reference voltage (+) = V_{BGR}
Reference voltage (-) = AV_{REFM}	Reference voltage (-) = V_{SS}	Reference voltage (-) = AV_{REFM}	Reference voltage (-) = AV_{REFM}
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI26	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		—

(1) When reference voltage (+) = AV_{REFP} /ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM} /ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, $\text{V}_{\text{SS}} = 0 \text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $\text{AV}_{\text{REFM}} = 0 \text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	± 3.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}		1.2	± 7.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.25	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 0.50	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 0.25	%FSR
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 2.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 5.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}}$ ^{Note 3}	1.8 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			± 1.5	LSB
			1.6 V $\leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ ^{Note 4}			± 2.0	LSB
Analog input voltage	V _{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage (2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, HS (high-speed main) mode)			V_{BGR} ^{Note 5}		V
		Temperature sensor output voltage (2.4 V $\leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$, HS (high-speed main) mode)			V_{TMPS25} ^{Note 5}		V

(Notes are listed on the next page.)

- (4) When reference voltage (+) = Internal reference voltage ($\text{ADREFP1} = 1$, $\text{ADREFP0} = 0$), reference voltage (-) = $\text{AV}_{\text{REFM}}/\text{ANI1}$ ($\text{ADREFM} = 1$), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

($T_A = -40$ to $+85^\circ\text{C}$, $2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$, $1.6 \text{ V} \leq EV_{\text{DD0}} = EV_{\text{DD1}} \leq V_{\text{DD}}$, $V_{\text{SS}} = EV_{\text{SS0}} = EV_{\text{SS1}} = 0 \text{ V}$, Reference voltage (+) = $\text{VBGR}^{\text{Note 3}}$, Reference voltage (-) = $\text{AV}_{\text{REFM}} = 0 \text{ V}^{\text{Note 4}}$, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit	
Conversion time	tconv	8-bit resolution	$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$			± 2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$			± 1.0	LSB
Analog input voltage	V _{Ain}			0		$\text{VBGR}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = V_{SS} , the MAX. values are as follows.

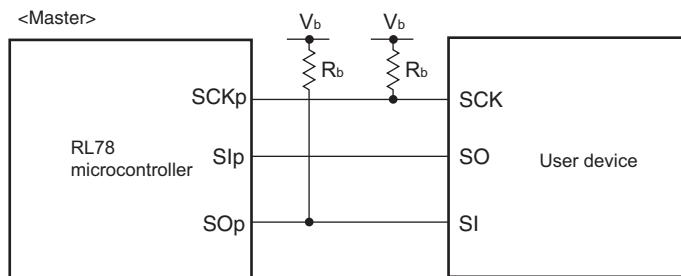
Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AV_{REFM} .

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM} .

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM} .

LVD Detection Voltage of Interrupt & Reset Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Interrupt and reset mode	V _{LVDA0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 0, falling reset voltage	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.60	1.63	1.66	V
	V _{LVDA1}			Falling interrupt voltage	1.74	1.77	1.81	V
	V _{LVDA2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.70	1.73	1.77	V
	V _{LVDA3}			Falling interrupt voltage	1.84	1.88	1.91	V
	V _{LVDB0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
	V _{LVDB1}			Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.94	1.98	2.02	V
	V _{LVDB3}			Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVDC0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
	V _{LVDC1}			Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVDC2}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
	V _{LVDC3}			Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVDD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.40	2.45	2.50	V
	V _{LVDD1}			Falling interrupt voltage	2.56	2.61	2.66	V
	V _{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.50	2.55	2.60	V
	V _{LVDD3}			Falling interrupt voltage	2.66	2.71	2.76	V
	V _{LVDD0}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.60	2.65	2.70	V
	V _{LVDD1}			Falling interrupt voltage	3.68	3.75	3.82	V
	V _{LVDD2}		LVIS1, LVIS0 = 1, 1	Rising release reset voltage	3.60	3.67	3.74	V
	V _{LVDD3}			Falling interrupt voltage	2.70	2.75	2.81	V

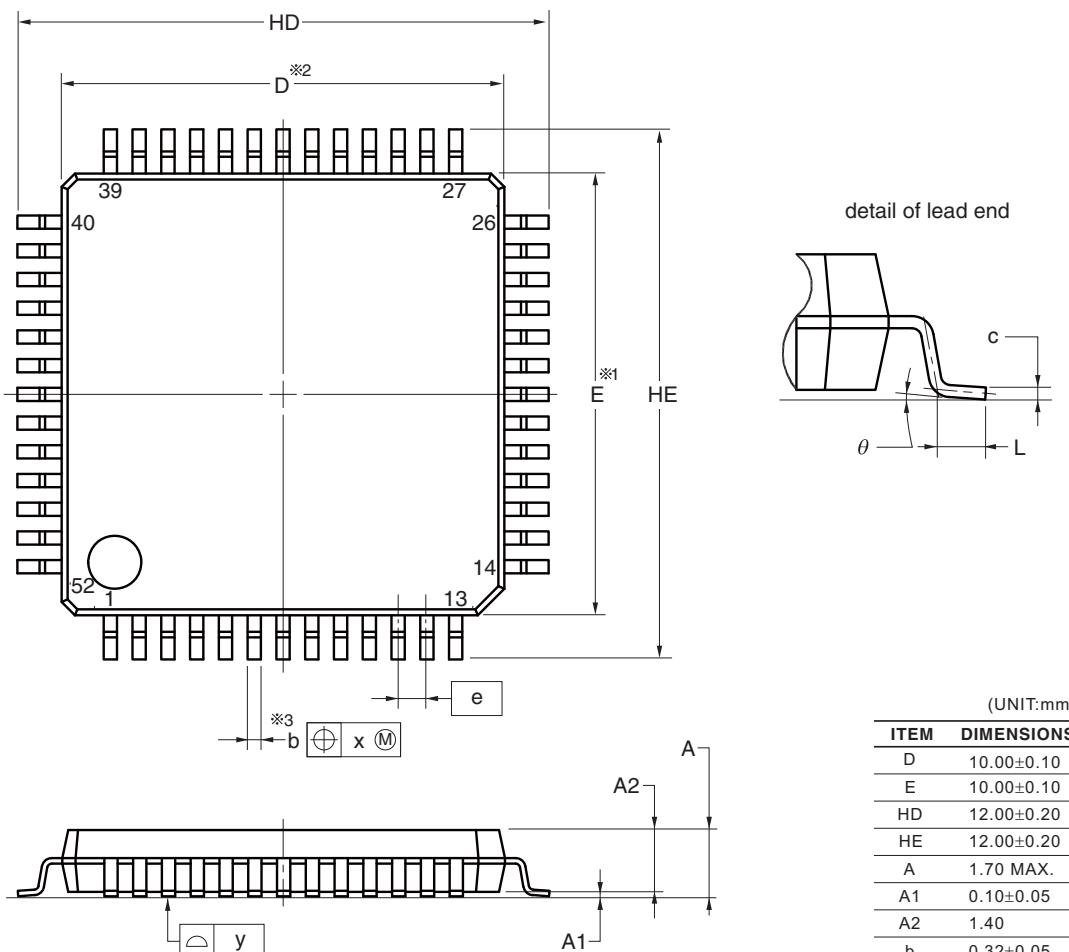
CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number , n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number ($mn = 00$))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAF, R5F100JFAFA, R5F100JGAF, R5F100JHAF, R5F100JJAF,
 R5F100JKAF, R5F100JLAF
 R5F101JCAFA, R5F101JDAFA, R5F101JEAF, R5F101JFAFA, R5F101JGAF, R5F101JHAF, R5F101JJAF,
 R5F101JKAF, R5F101JLAF
 R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JGDFA, R5F100JHDFA, R5F100JJDF,
 R5F100JKDFA, R5F100JLDFA
 R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JGDFA, R5F101JHDFA, R5F101JJDF,
 R5F101JKDFA, R5F101JLDFA
 R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



(UNIT:mm)	
ITEM	DIMENSIONS
D	10.00±0.10
E	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
A	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32±0.05
c	0.145±0.055
L	0.50±0.15
θ	0° to 8°
e	0.65
x	0.13
y	0.10

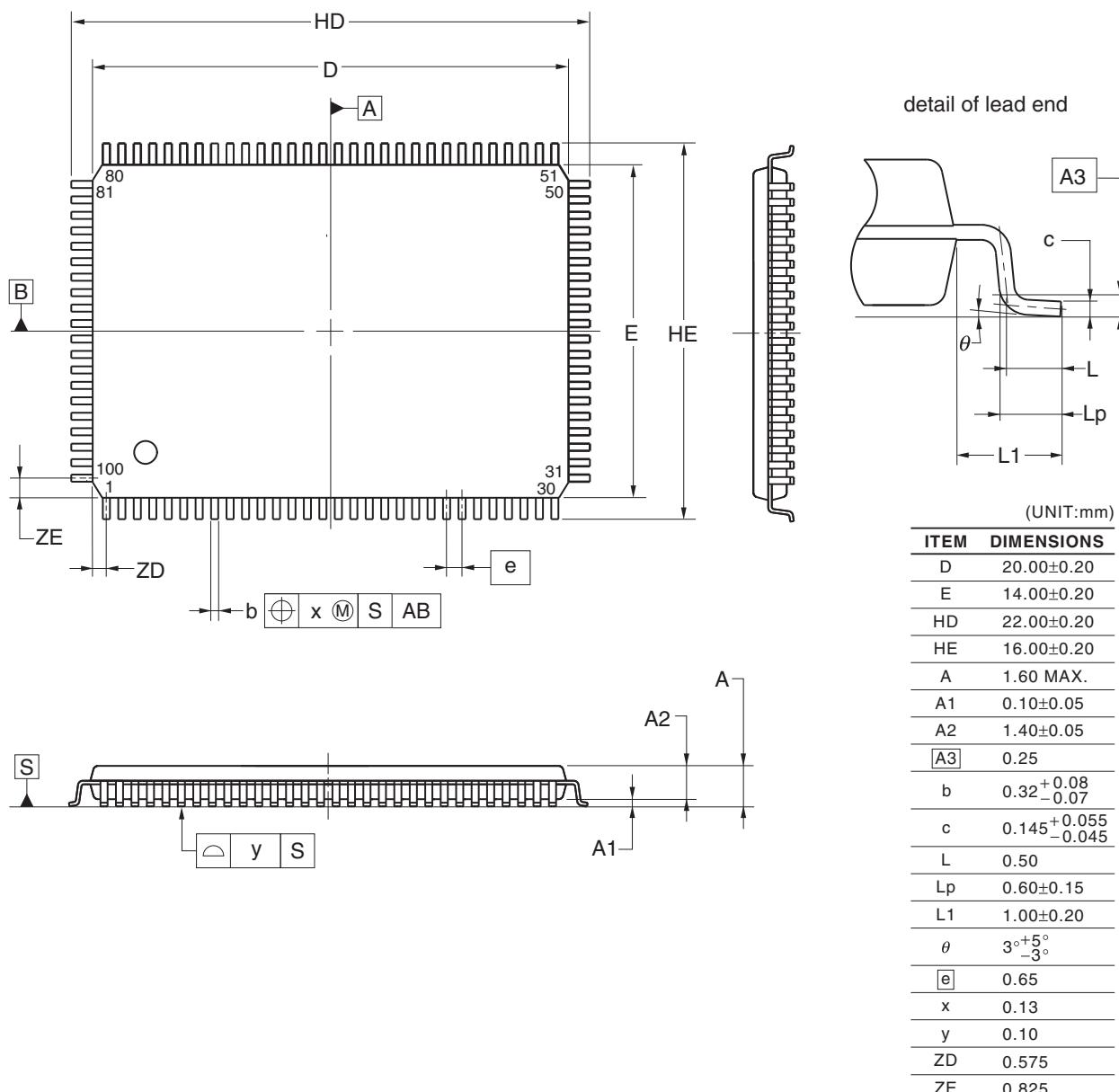
NOTE

1. Dimensions “*1” and “*2” do not include mold flash.
2. Dimension “*3” does not include trim offset.

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R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA
 R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA
 R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJ DFA, R5F100PK DFA, R5F100PL DFA
 R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJ DFA, R5F101PK DFA, R5F101PL DFA
 R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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Revision History		RL78/G13 Data Sheet	
Rev.	Date	Description	
		Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing